Unit: mm

T OSHIBA Field Effect Transistor with Built-in Schottky Barrier Diode Silicon N-Channel MOS Type (Ultra-High-Speed U-MOS Ⅲ)

TPC8A02-H

High-Efficiency DC/DC Converter Applications

Notebook PC Applications

Portable-Equipment Applications

- Built-in Schottky barrier diode
 Low forward voltage: V_{DSF} = 0.6V (max)
- · High-speed switching.
- Small gate charge.: QSW = 11 nC (typ.)
- Low drain-source ON-resistance: RDS (ON) = 4.3 m Ω (typ.)
- High forward transfer admittance: $|Y_{fs}| = 40 \text{ S (typ.)}$
- Low leakage current: $IDSS = 100 \mu A (max) (VDS = 30 V)$
- Enhancement mode: $V_{th} = 1.1$ to 2.3 V ($V_{DS} = 10$ V, $I_{D} = 1$ mÅ).

Absolute Maximum Ratings (Ta = 25°C)

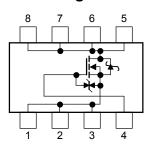
Characteristic		Symbol	Rating	Unit
Drain-source voltage		V _{DSS} \langle	30	V
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V_{DGR}	30	X
Gate-source voltage		V _{GSS}	±20	V
Drain current	DC (Note 1)	ID	16	A
	Pulse (Note 1)	E E	48	\nearrow A
Drain power dissipation (t = 10 s) (Note 2a)		PD	1.9	W
Drain power dissipation (t = 10 s) (Note 2b)		PD	1.0	W
Single-pulse avalanche energy (Note 3)		EAS	166	mJ
Avalanche current		I _{AR}	16	Α
Repetitive avalanche energy (Note 2a) (Note 4)		EAR	0.11	mJ
Channel temperature		T _{ch}	150	°C
Storage temperature range		T _{\$tg}	-55 to 150	°C

0.595T/P 1.22 0.595T

Weight: 0.085 g (typ.)

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Circuit Configuration



2-6J1B

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

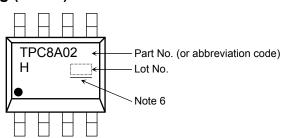
This transistor is an electrostatic-sensitive device. Handle with care. Schottky barrier diodes have large-reverse-current-leakage characteristic compared to other rectifier products. This current leakage combined with improper operating temperature or voltage may cause thermal runaway. Please take forward and reverse loss into consideration during design.

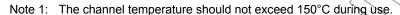
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Thermal Characteristics

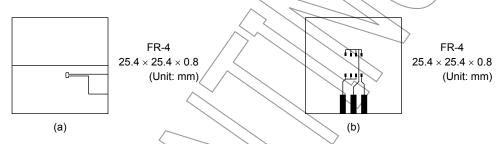
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R _{th (ch-a)}	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R _{th (ch-a)}	125	°C/W

Marking (Note 5)





Note 2: (a) Device mounted on a glass-epoxy board (b) Device mounted on a glass-epoxy board (b)

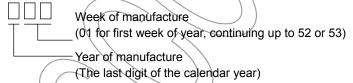


Note 3: $V_{DD} = 24 \text{ V}$, $T_{ch} = 25^{\circ}\text{C}$ (initial), L = 1.0 mH, $R_{G} = 25 \Omega$, $I_{AR} = 7 \text{ A}$

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: • on the lower left of the marking indicates Pin 1.

* Weekly code: (Three digits)



Note 6: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

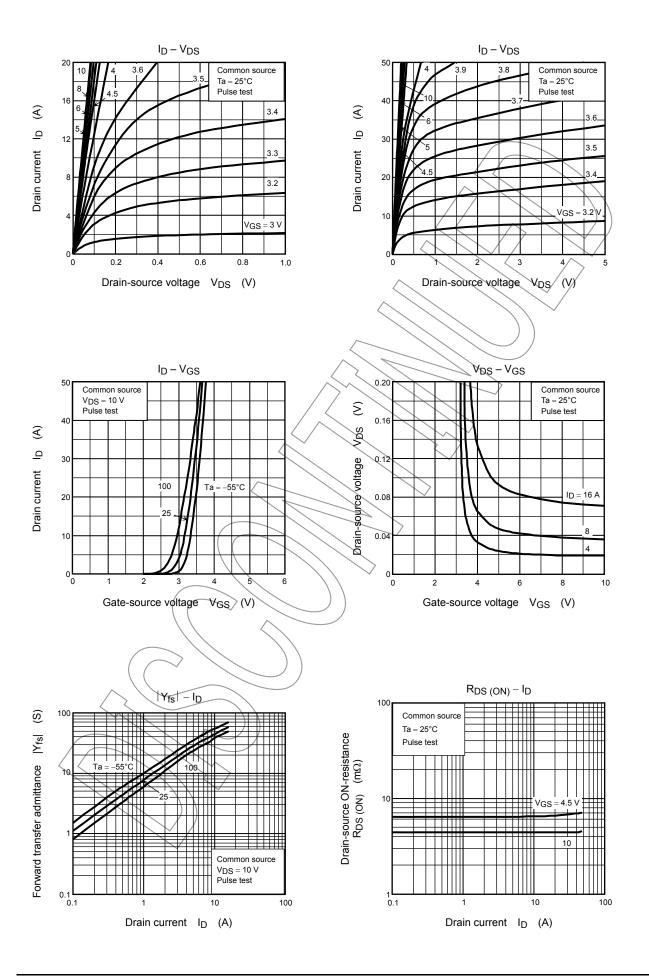
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

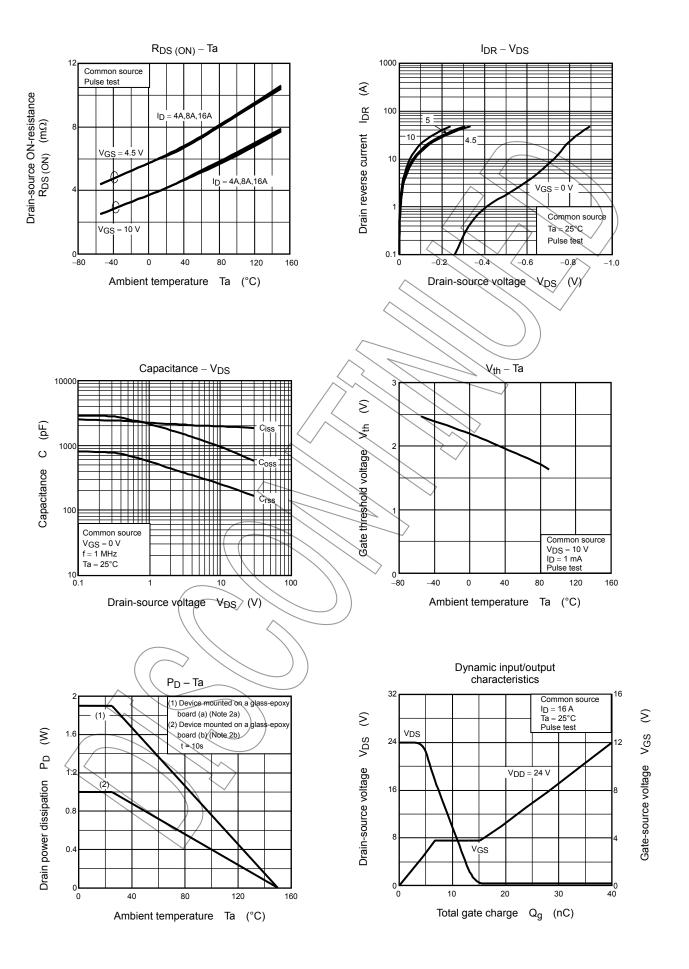
Electrical Characteristics (Ta = 25°C)

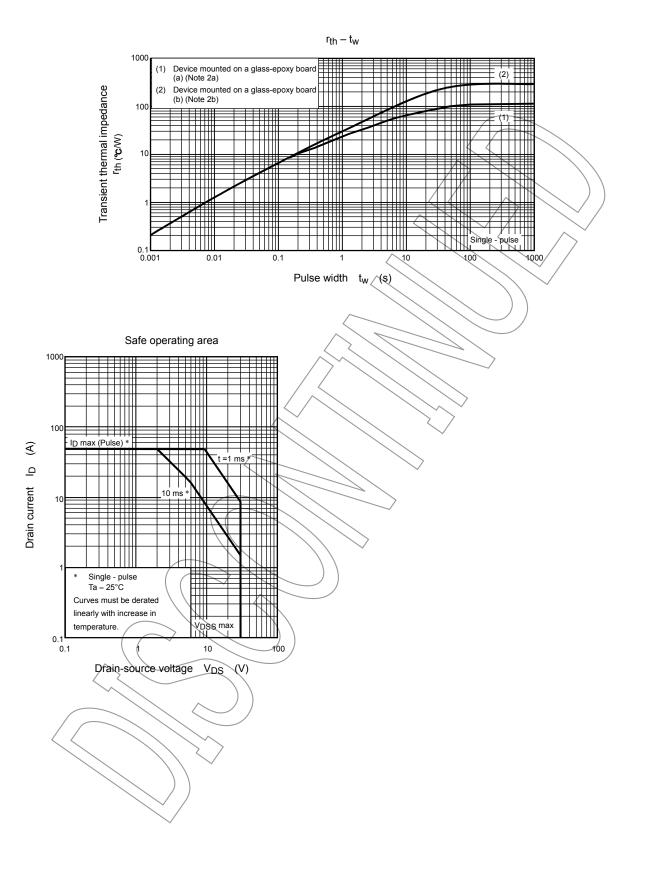
Chai	racteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curre	ent	I _{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±10	μА
Drain cutoff current	t	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V		_	100	μА
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_		V
		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_		V
Gate threshold volt	age	V _{th}	V _{DS} = 10 V, I _D = 1 mA	/1.1		2.3	V
Drain-source ON-resistance		Б	V _{GS} = 4.5 V, I _D = 8 A	<u></u>	6.2	8.5	m()
Drain-source ON-16	esisiance	R _{DS} (ON)	V _{GS} = 10 V, I _D = 8 A	7/	4.3	5.6	mΩ
Forward transfer a	dmittance	Y _{fs}	V _{DS} = 10 V, I _D = 8 A	20	40	+)	S
Input capacitance		C _{iss}		/-/	1970	$\langle - \rangle$	
Reverse transfer ca	apacitance	C _{rss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	<	240/	>_	pF
Output capacitance		Coss		/_/	950 /	_	
Switching time	Rise time	t _r	V _{GS} 10 V I _D = 8 A V _{OUT}	+	6		
	Turn-on time	t _{on}	OV J CONTINUE OF STATE OF STAT		14		no
	Fall time	t _f		>-	12		ns
	Turn-off time	t _{off}	Duty ≤ 1%, t _w = 10 µs	_	26		
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \simeq 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D \neq 16 \text{ A}$	_	34	_	-
			$V_{DD} \simeq 24 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 16 \text{ A}$	_	19	_	
Gate-source charge 1		Q _{gs1}		_	6		nC
Gate-drain ("Miller") charge		Q _{gd}	$V_{DD} \simeq 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 16 \text{ A}$	_	8.4	_	
Gate switch charge		Q _{sw}		_	11		

Source-Drain Ratings and Characteristics (Ta = 25°C)

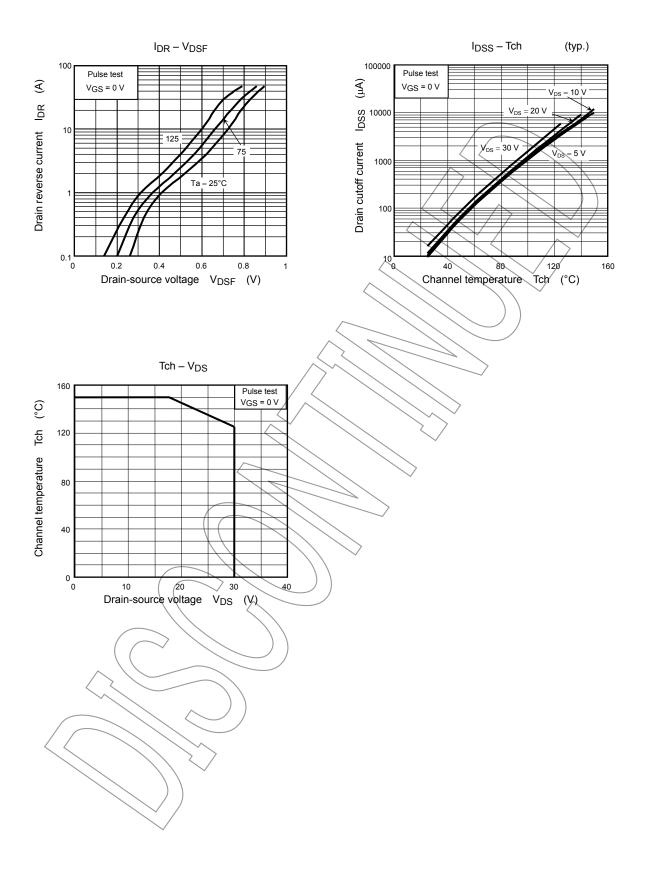
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Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Peak forward current Pulse (N	Note 1) IFP	_	_	_	48	Α
Forward voltage (diade)	Vacs	I _{DR} = 1.0 A, V _{GS} = 0 V	_	-0.45	-0.6	V
Forward voltage (diode)	V _{DSF}	I _{DR} = 16 A, V _{GS} = 0 V	_	_	-1.2	V







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